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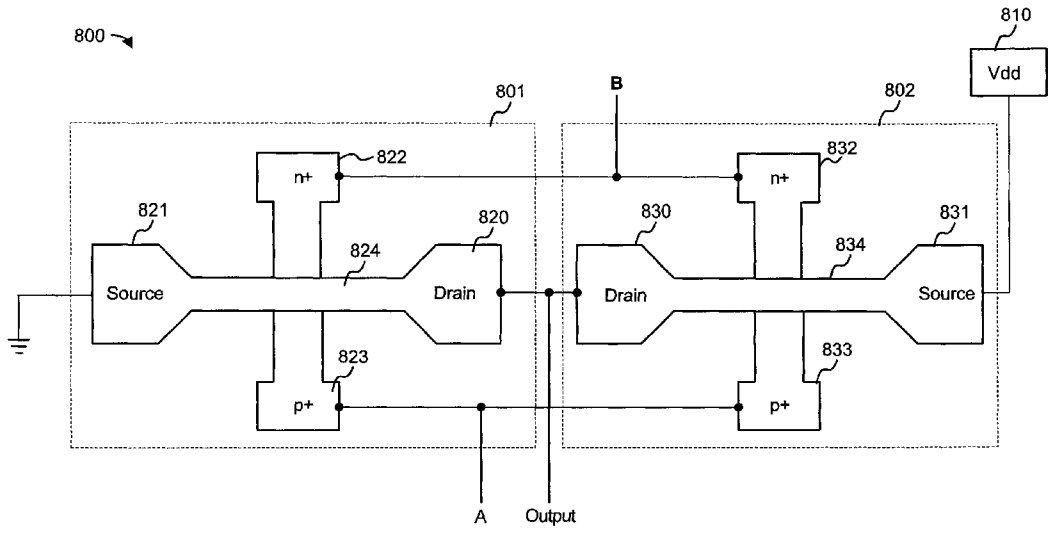
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(54) Title: TWO TRANSISTOR NOR DEVICE



(57) Abstract: A NOR gate includes is constructed with two asymmetric FinFET type transistors (801, 802) instead of the conventional four-transistor NOR gate. The reduction in the number of transistors from four down to two allows for significant improvements in integrated semiconductor circuits.

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